

Title (en)

PATTERNED INTEGRATED CIRCUIT AND METHOD OF PRODUCTION THEREOF

Title (de)

STRUKTURIERTE INTEGRIERTE SCHALTUNG UND HERSTELLUNGSVERFAHREN DAFÜR

Title (fr)

CIRCUIT INTÉGRÉ À MOTIFS ET PROCÉDÉ DE PRODUCTION DE CELUI-CI

Publication

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Application

**EP 09771083 A 20090626**

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Abstract (en)

[origin: WO2009158552A1] The present invention relates generally to the field of integrated electronics. More specifically, the present invention relates to patterned graphene-like carbon-based integrated circuits and methods of production thereof. Methods of photo-, electron-beam projection, extreme-ultraviolet, and imprint lithographic patterning and also several thermal patterning methods are disclosed in the present invention.

IPC 8 full level

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Citation (search report)

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- [X] GU GONG ET AL: "Field effect in epitaxial graphene on a silicon carbide substrate", APPLIED PHYSICS LETTERS, AIP, AMERICAN INSTITUTE OF PHYSICS, MELVILLE, NY, US, vol. 90, no. 25, 19 June 2007 (2007-06-19), pages 253507 - 253507, XP012095422, ISSN: 0003-6951, DOI: 10.1063/1.2749839
- [A] F. MOLITOR ET AL: "Local gating of a graphene Hall bar by graphene side gates", PHYSICAL REVIEW B, vol. 76, no. 24, 1 December 2007 (2007-12-01), XP055034729, ISSN: 1098-0121, DOI: 10.1103/PhysRevB.76.245426
- See references of WO 2009158552A1

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